
2SJ530(L), 2SJ530(S)

Silicon P Channel MOS FET
High Speed Power Switching

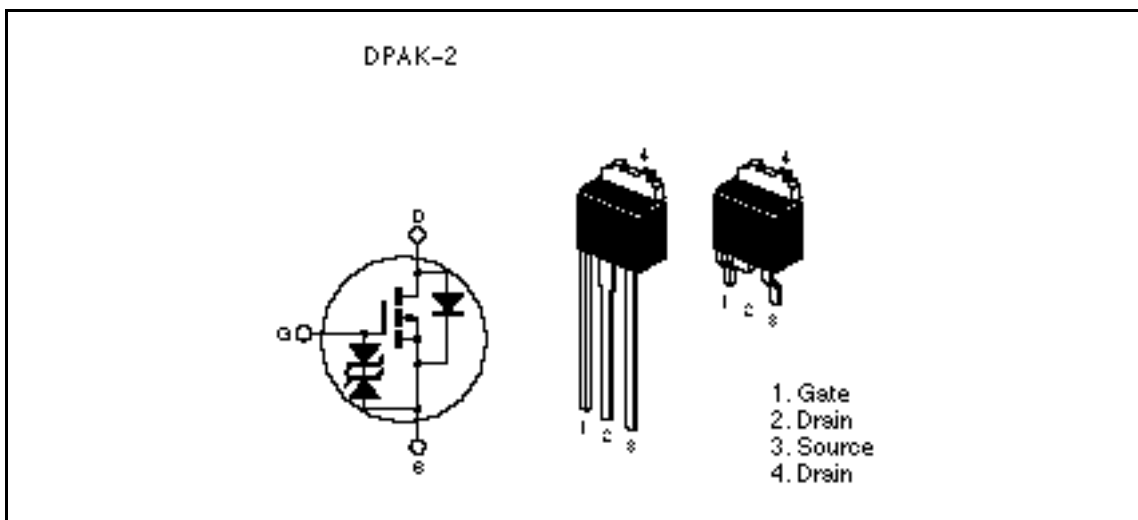
HITACHI

ADE-208-655B (Z)
3rd. Edition
Jun 1998

Features

- Low on-resistance
 $R_{DS(on)} = 0.08$ typ.
- 4V gate drive devices.
- High speed switching.

Outline



2SJ530(L),2SJ530(S)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	-15	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	-60	A
Body-drain diode reverse drain current	I_{DR}	-15	A
Avalanche current	I_{AP} ^{Note3}	-15	A
Avalanche energy	E_{AR} ^{Note3}	19	mJ
Channel dissipation	P_{ch} ^{Note2}	30	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

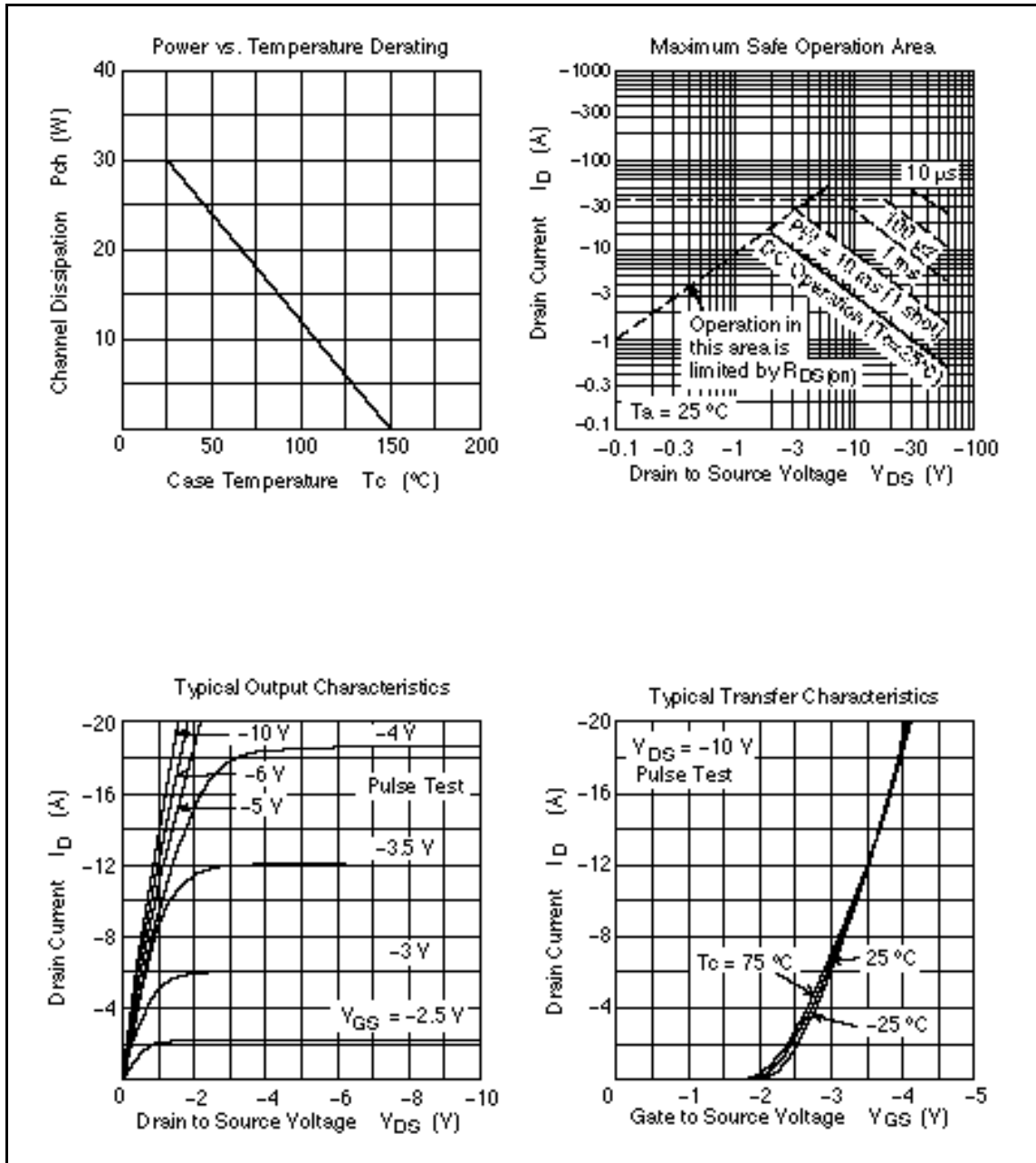
Note: 1. PW 10µs, duty cycle 1 %
 2. Value at Tc = 25°C
 3. Value at Tch = 25°C, Rg 50

Electrical Characteristics (Ta = 25°C)

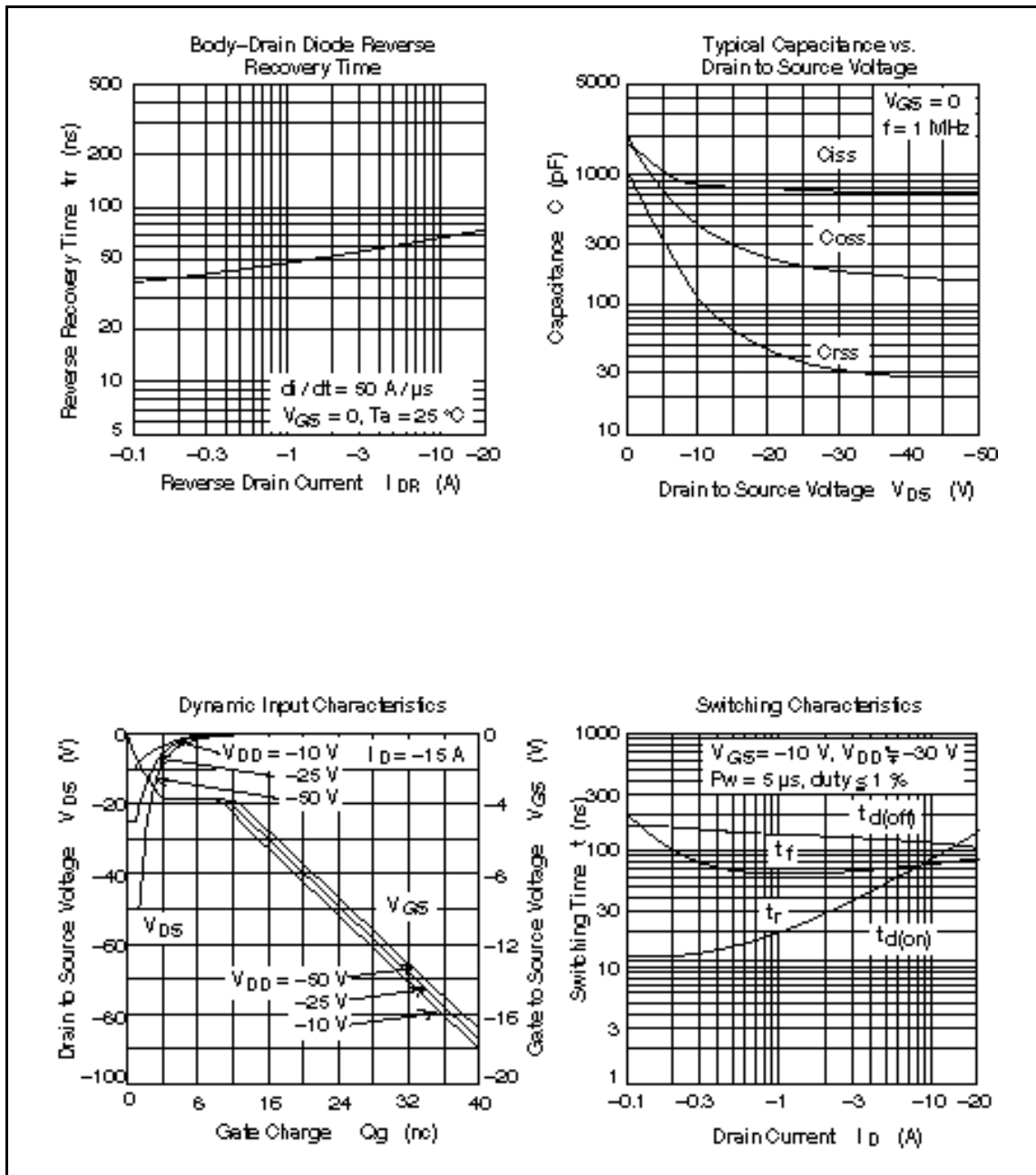
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = ±100µA, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-10	µA	$V_{DS} = -60V, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	µA	$V_{GS} = ±16V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1mA, V_{DS} = -10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.08	0.10		$I_D = -8A, V_{GS} = -10V$ ^{Note4}
	$R_{DS(on)}$	—	0.11	0.16		$I_D = -8A, V_{GS} = -4V$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	6.5	11	—	S	$I_D = -8A, V_{DS} = -10V$ ^{Note4}
Input capacitance	C_{iss}	—	850	—	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	—	420	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	110	—	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	12	—	ns	$V_{GS} = -10V, I_D = -8A$
Rise time	t_r	—	75	—	ns	$R_L = 3.75$
Turn-off delay time	$t_{d(off)}$	—	125	—	ns	
Fall time	t_f	—	75	—	ns	
Body-drain diode forward voltage	V_{DF}	—	-1.1	—	V	$I_F = -15A, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	70	—	ns	$I_F = -15A, V_{GS} = 0$ diF/ dt =50A/µs

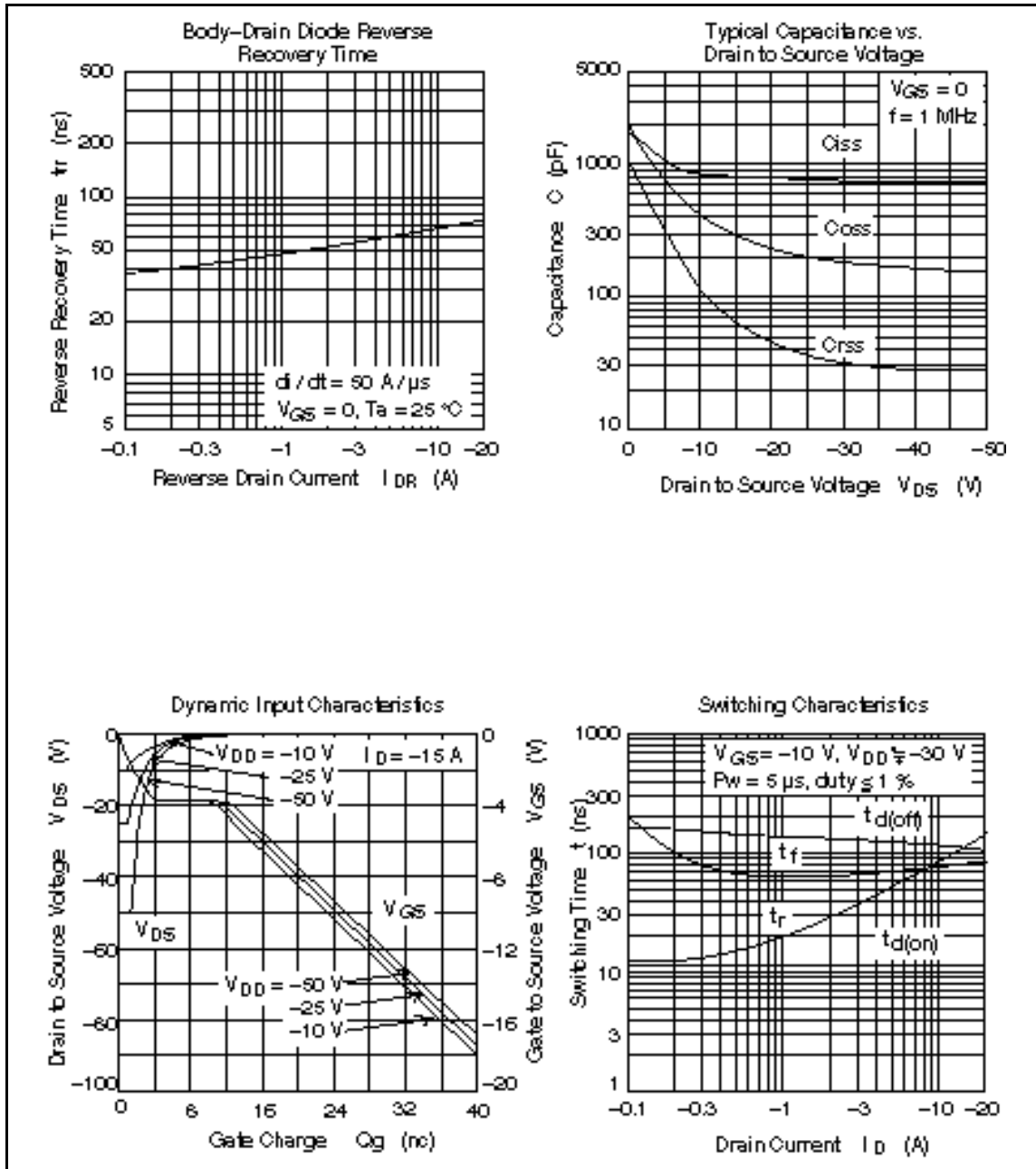
Note: 4. Pulse test

Main Characteristics

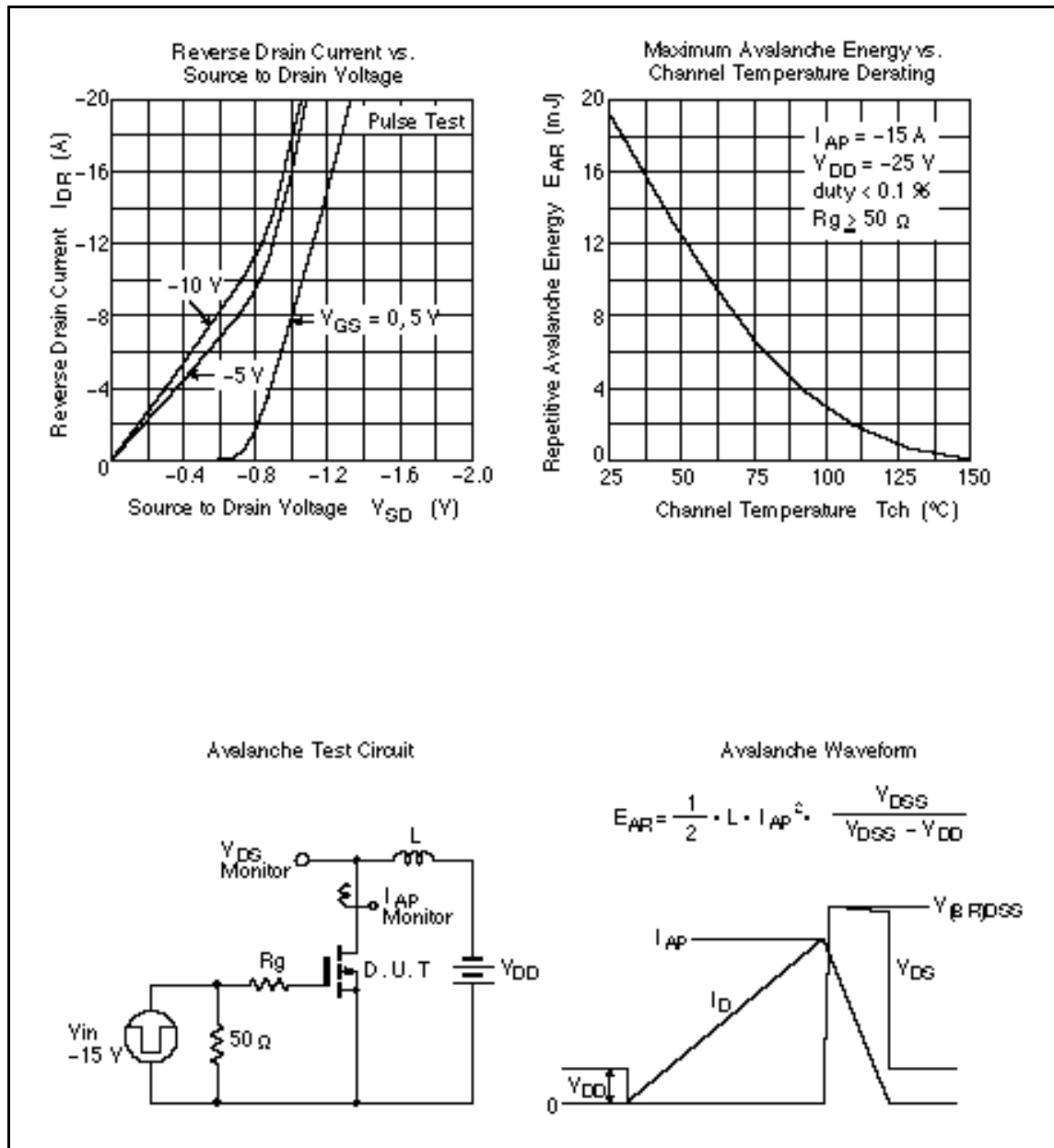


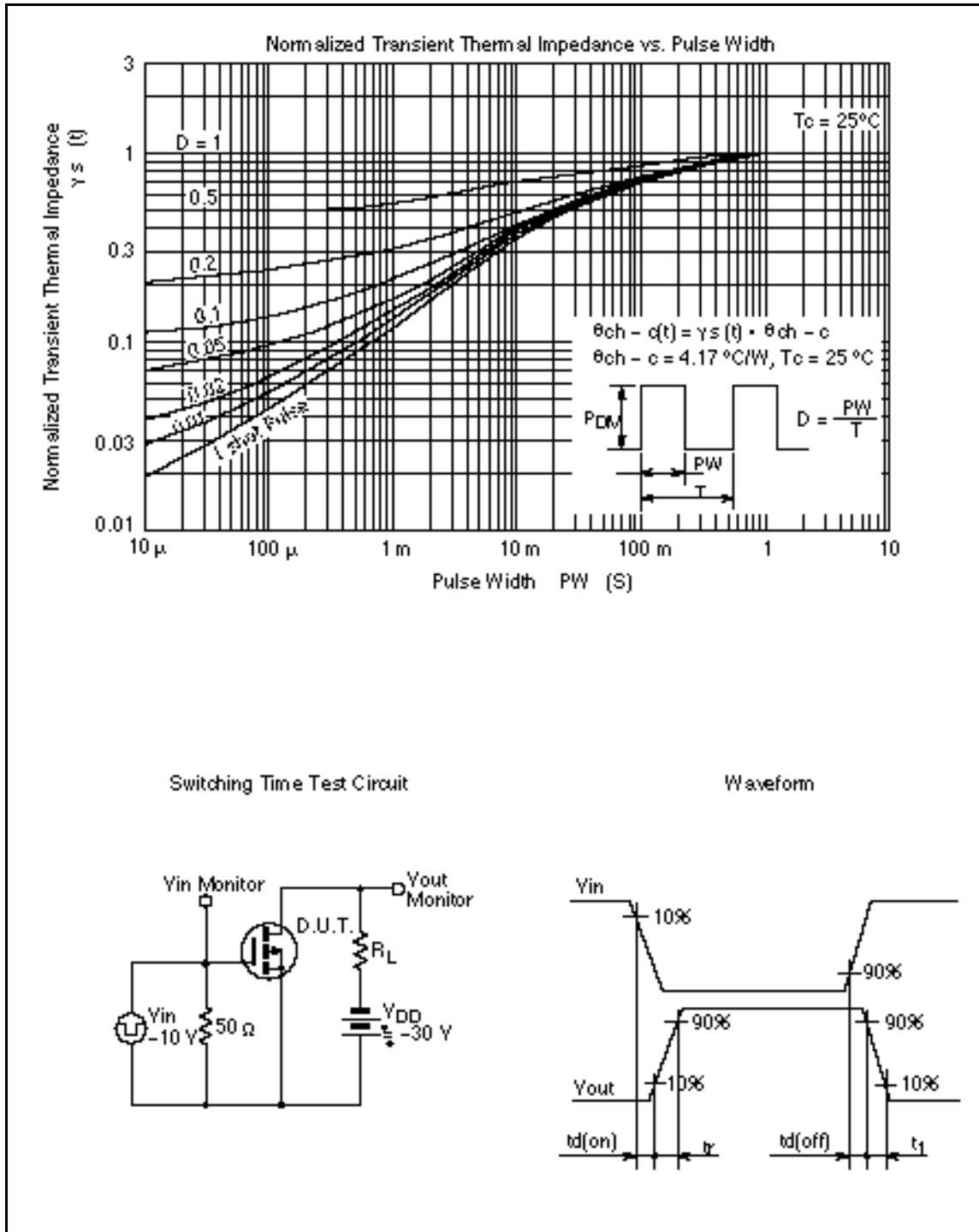
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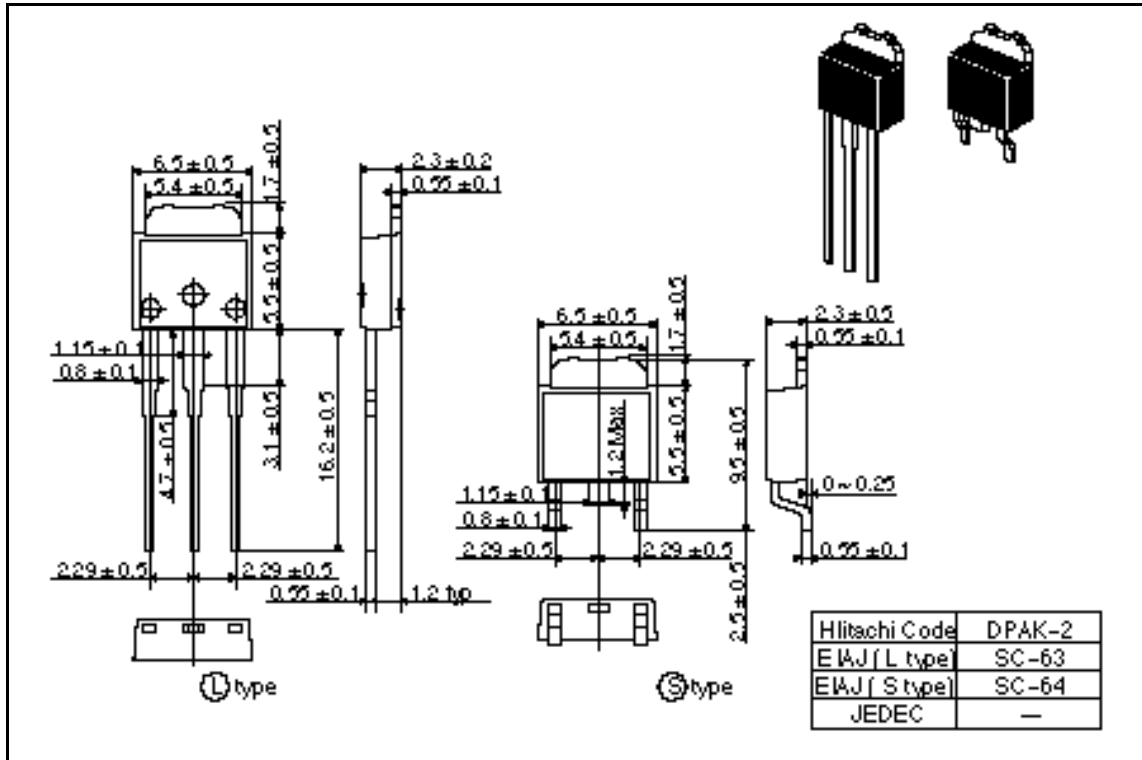




2SJ530(L),2SJ530(S)

Package Dimensions

Unit: mm



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HITACHI**Hitachi, Ltd.**

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohie-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 8270-2111
Fax: (03) 8270-5109

For further information write to:

Hitachi Semiconductor
(America) Inc.
2000 Sierra Point Parkway
Brisbane, CA 94005-1897
U.S.A.
Tel: 800-285-1601
Fax: 808-297-0447

Hitachi Europe GmbH
Continental Europe
Domagala Straße 8
D-85622 Feldkirchen
München
Tel: 089-931 80-0
Fax: 089-929 80-00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 01628-585000
Fax: 01628-585160

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049818
Tel: 535-2100
Fax: 535-1538

Hitachi Asia (Hong Kong) Ltd.
Unit 1706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27859218
Fax: 27806071

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